

PRELIMINARY DATA SHEET

NEC

NPN SILICON EPITAXIAL TRANSISTOR

NE68939

FEATURES

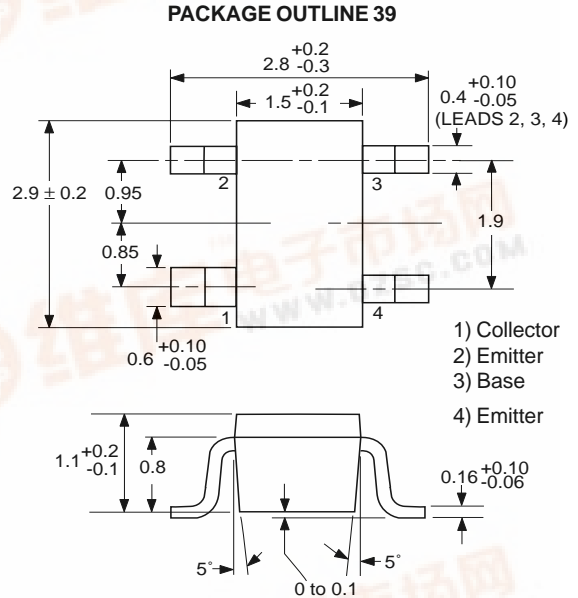
- **OUTPUT POWER AT 1dB COMPRESSION POINT:**
24.5 dBm TYP @F = 1.9 GHz, V_{CE} = 3.6 V, Class AB, Duty 1/8
- **4 PIN MINI MOLD PACKAGE:** NE68939

DESCRIPTION

The NE68939 is a low voltage, NPN Silicon Bipolar Transistor for pulsed power applications. The device is designed to operate from a 3.6 V supply, and deliver over 1/4 watt of power output at frequencies up to 2.0 GHz with a 1:8 duty cycle. These characteristics make it an ideal device for TX driver stage in a 1.9 GHz digital cordless telephone (DECT or PHS). The part is supplied in a SOT-143 (SC-61) 4-pin Mini-mold package and is available on tape and reel.

The NE68939 transistors are manufactured to NEC's stringent quality assurance standards to ensure highest reliability and consistent superior performance.

OUTLINE DIMENSIONS (Units in mm)



ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

PART NUMBER		NE68939			
PACKAGE CODE		39			
SYMBOLS	PARAMETERS	UNITS	MIN	TYP	MAX
I _{CBO}	Collector Cutoff Current, V _{CB} = 5 V, I _E = 0	μA			2.5
I _{EBO}	Emitter Cutoff Current, V _{EB} = 1 V, I _C = 0	μA			2.5
h _{FE}	DC Current Gain, V _{CE} = 3.6 V, I _C = 100 mA		30		
P-1	Output Power	V _{CE} = 3.6 V, f = 1.9 GHz I _{CQ} = 2 mA (Class AB) Duty 1/8		24.5	
G _p	Power Gain			8	
η _C	Collector Efficiency			62	
T _{ON}	Maximum Device On Time	Ms			10.0



NE68939

ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25 °C)

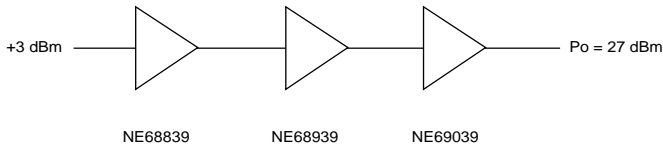
SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{CBO}	Collector to Base Voltage	V	9.0
V _{CEO}	Collector to Emitter Voltage	V	6.0
V _{EBO}	Emitter to Base Voltage	V	2.0
I _C	Collector Current mA	150	
P _T	Total Power Dissipation	mW	200 (CW)
T _j	Junction Temperature	°C	150
T _{STG}	Storage Temperature	°C	-65 to +150

Note:

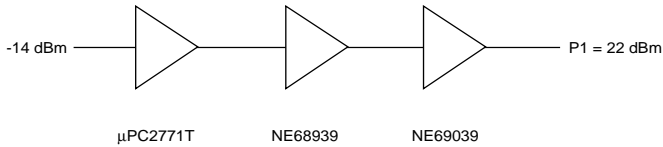
- Operation in excess of any one of these parameters may result in permanent damage.

APPLICATION

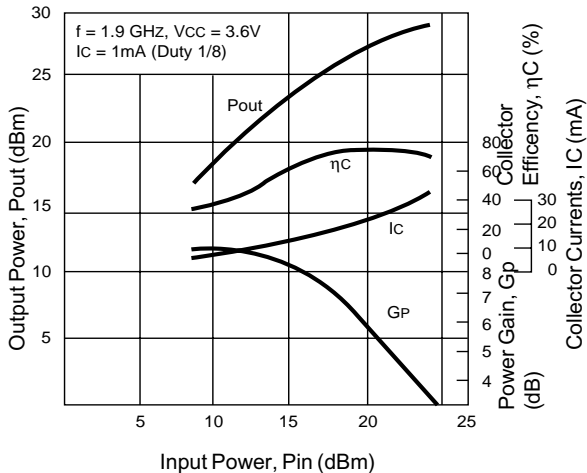
(1) TX Amplifier for DECT



(2) TX Amplifier for PHS



OUTPUT POWER, COLLECTOR EFFICIENCY, COLLECTOR CURRENT AND POWER GAIN VS. INPUT POWER

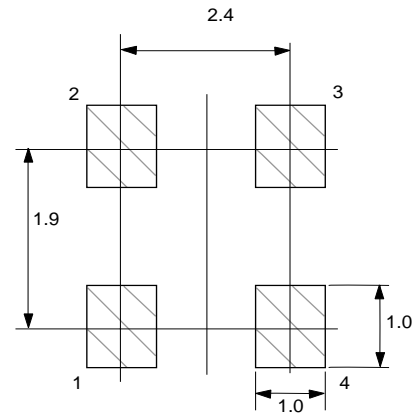


TYPICAL DATA

f = 1.9 GHz, V_{CC} = 3.6 V, I_{CQ} = 1 mA, DUTY = 1/8

P _{1dB}	24.5	dbm
η _C	62	%
I _C	15	mA
GL	9.0	db

OUTLINE 39 RECOMMENDED P.C.B. LAYOUT



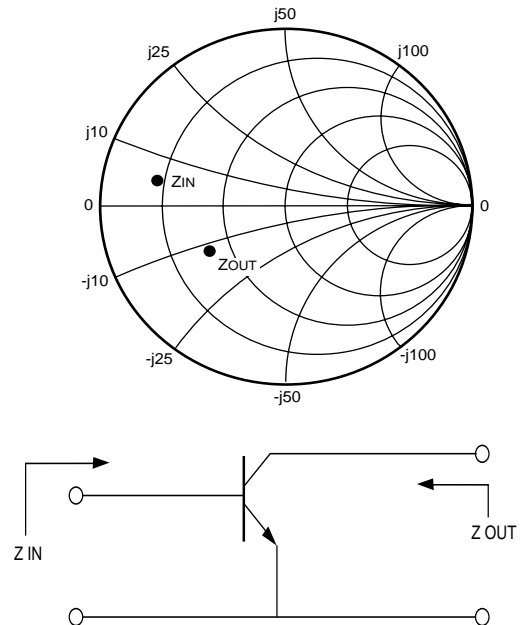
ORDERING INFORMATION

PART NUMBER	QTY
NE68939-T1	3K/REEL

Note:

- Lead material: Cu
Lead plating: PbSn

Z_{IN} (Ω), Z_{OUT} (Ω) DATA



IMPEDANCE LOOKING INTO DEVICE V_{CC} = 3.6 V, I_{CQ} = 1 mA, CLASS AB

FREQUENCY (GHz)	Z _{IN} (Ω)	Z _{OUT} (Ω)
1.9	7.85+j5.62	21.9-j11.6
0.9	3.1+j11.6	5.3-j5.7

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